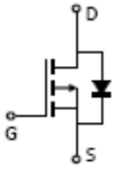
SOT-23 -3Plastic-Encapsulate Transistors

2301 MOSFET(P-Channel)

FEATURES

TrenchFET Power MOSFET



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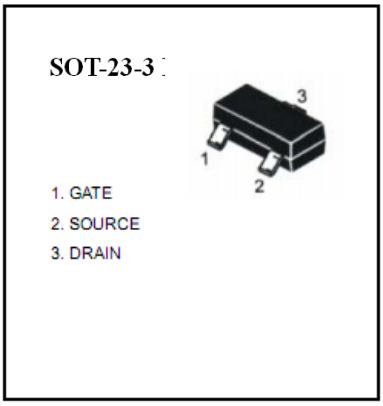

MAXIMUM RATINGS (TA=25℃ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{DS}	Drain-Source voltage	-20	V
V_{GS}	Gate-Source voltage	±12	V
I_D	Drain current	-3	A
P_D	Power Dissipation	1	W
Tj	Junction Temperature	150	℃
Tstg	Storage Temperature	-55-150	℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V,I_D=-250uA	-20			V
Gate-Threshold Voltage	$V_{th(GS)}$	V_{DS}= V_{GS}, I_D=-250 uA	-0.4	-0.7	-1	V
Gate-body Leakage	I_{GSS}	V_{DS}=0V, V_{GS}=±12V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-20V, V_{GS}=0V			-1	uA
Drain-Source On-Resistance	$r_{DS(ON)}$	V_{GS}=-4.5V, I_D=-3A		64	110	mΩ
		V_{GS}=-2.5V, I_D=-2A		89	140	mΩ
Forward Trans conductance	gfs	V_{DS}=-5V, I_D=-2.8A		9.5		s
Dynamic Characteristics						
Input Capacitance	Ciss	V_{DS}=-10V, V_{GS}=0V, f=1MHz		405		pF
Output Capacitance	Coss			75		
Reverse Transfer Capacitance	Crss			55		
Switching Capacitance						
Turn-on Delay Time	td(on)	V_{DD}=-10V, I_D=-1A, V_{GS}=-4.5V R_{GEN}=10Ω		11		nS
Turn-on Rise Time	t_r			35		nS
Turn-off Delay Time	td(off)			30		nS
Turn-off Fall Time	t_f			10		nS
Total Gate Charge	Q_g	V_{DS}=-10V, I_D=-3A, V_{GS}=-2.5V,		3.3	12	nC
Gate-Source Charge	Q_{gs}			0.7		nC
Gate-Drain Charge	Q_{gd}			1.3		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage	V_{SD}	V_{GS}=0V, I_D=-1.3A			-1.2	V
Diode Forward Current	Is				-1.3	A

Typical Characteristics 2301

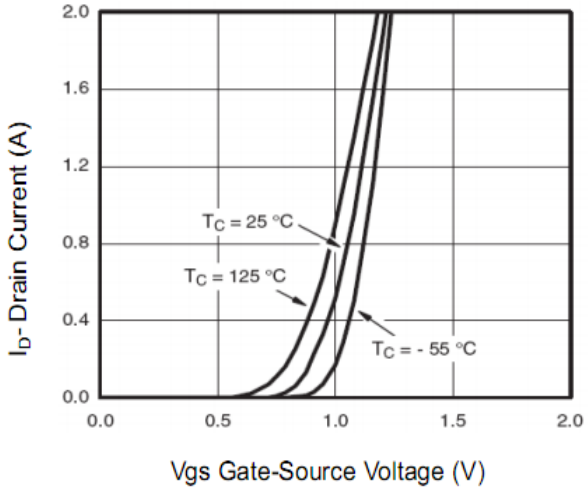

Figure 7 Transfer Characteristics

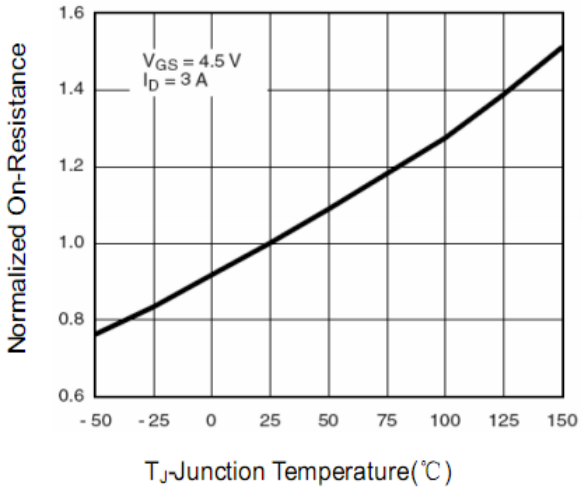

Figure 8 Drain-Source On-Resistance

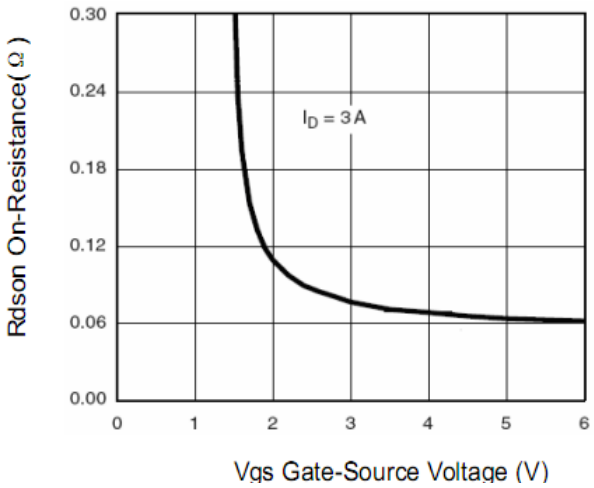

Figure 9 Rdson vs Vgs

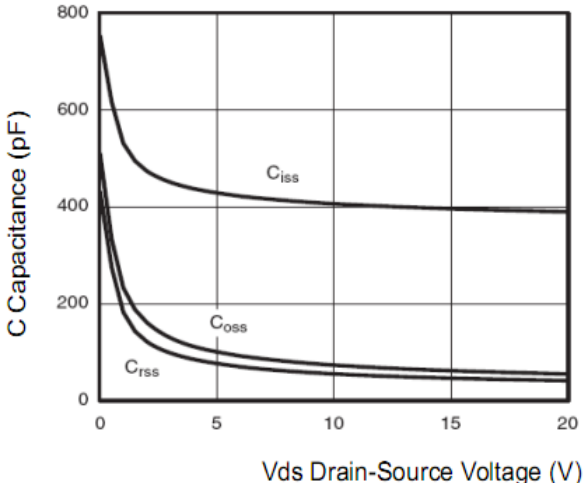

Figure 10 Capacitance vs Vds

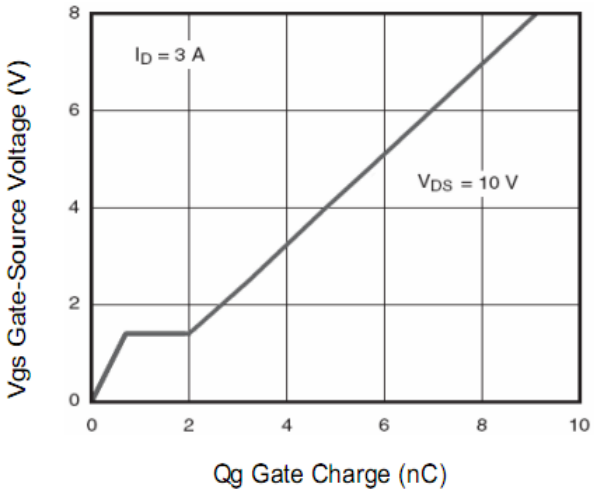

Figure 11 Gate Charge

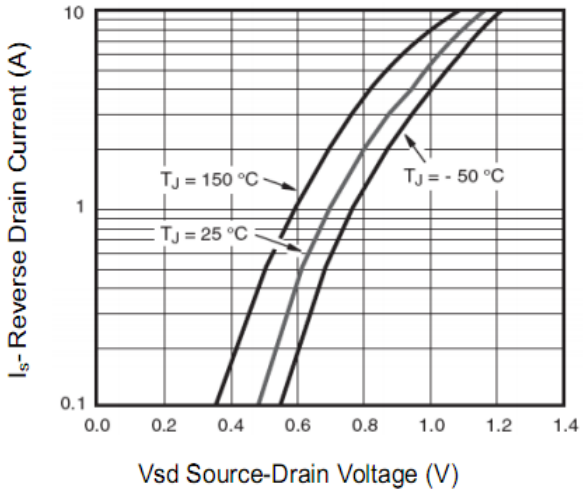

Figure 12 Source- Drain Diode Forward